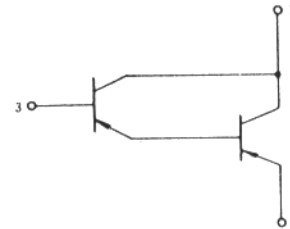
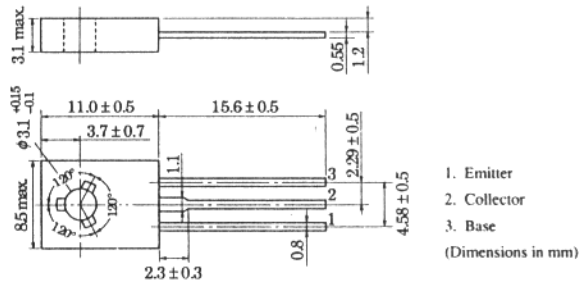


## 2SA1194 (K)

SILICON PNP EPITAXIAL  
HIGH GAIN AMPLIFIER



1. Emitter  
2. Collector  
3. Base  
(Dimensions in mm)

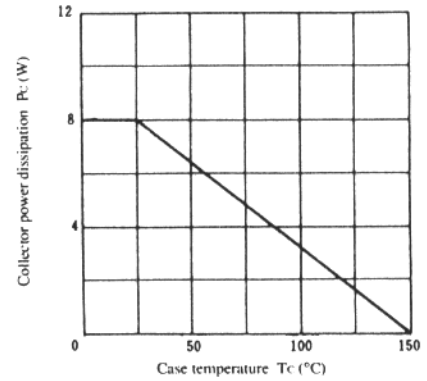
(JEDEC TO-126 MOD.)

### ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1194 (K)	Unit
Collector to base voltage	VCBO	-60	V
Collector to emitter voltage	VCEO	-60	V
Emitter to base voltage	VEBO	-7	V
Collector current	IC	-1	A
Collector peak current	iC(peak)	-2	A
Collector power dissipation	PC	1	W
	PC*	8	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

\* Value at Tc = 25°C

### MAXIMUM COLLECTOR DISSIPATION CURVE



### ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V(BR)CEO	IC = -1mA, RBE = ∞	-60	—	—	V
Collector cutoff current	ICBO	VCB = -60V, IE = 0	—	—	-1.0	μA
Emitter cutoff current	IEBO	VEB = -7V, IC = 0	—	—	-1.0	μA
DC current transfer ratio	hFE	VCE = -3V, IC = -500mA*	1000	—	—	
Collector to emitter saturation voltage	VCE(sat)	IC = -500mA, IB = -1mA*	—	—	-2.0	V
Base to emitter saturation voltage	VBE(sat)		—	—	-2.0	V
Turn on time	ton	IC = -500mA	—	0.7	—	μs
Turn off time	toff	IB1 = -IB2 = -1mA	—	0.8	—	μs

\* Pulse Test

